

What is claimed is:

1 1. A method comprising:

2 forming a source drain extension by implanting
3 boron, carbon, and fluorine.

1 2. The method of claim 1 including implanting carbon
2 to a depth deeper than the boron implant.

1 3. The method of claim 2 including implanting
2 fluorine to a depth deeper than the boron implant.

1 4. The method of claim 1 including implanting carbon
2 at an energy of about 6 KeV.

1 5. The method of claim 4 including implanting carbon
2 at a dose of about 1E15 atoms/cm².

1 6. The method of claim 1 including performing a Halo
2 implant before the implanting boron.

1 7. A method comprising:

2 implanting boron and fluorine to form a source
3 drain extension; and

4 implanting an additional species to reduce
5 transient enhanced diffusion of boron.

1 8. The method of claim 7 including implanting carbon
2 as said additional species.

1 9. The method of claim 8 including implanting carbon
2 to a depth deeper than the boron implant.

1 10. The method of claim 9 including implanting
2 fluorine to a depth deeper than the boron implant.

1 11. The method of claim 8 including implanting carbon
2 at an energy of about 6 KeV.

1 12. The method of claim 11 including implanting
2 carbon at a dose of about 1E15 atoms/cm².

1 13. The method of claim 7 including performing a Halo
2 implant before implanting boron.

1 14. An integrated circuit comprising:
2 a P-type transistor having a source drain
3 extension including carbon and boron.

1 15. The circuit of claim 14 wherein said extension
2 includes fluorine.

1 16. The circuit of claim 14 wherein carbon is deeper
2 than said boron.

3 17. The circuit of claim 14 wherein fluorine is
4 deeper than said boron.

1 18. A method comprising:
2 performing an Arsenic Halo implant before
3 implanting to form P-type source/drain extensions.

1 19. The method of claim 18 including forming the P-
2 type source/drain extensions using boron, carbon, and
3 fluorine implants.

1 20. The method of claim 18 including implanting
2 carbon to a depth deeper than the boron implant.

1 21. The method of claim 20 including implanting
2 fluorine to a depth deeper than the boron implant.